

applications of Ni₃Al-based alloys the authors recommend further research and development in a number of specific areas of the structure-property-processing relationships (Chapter 2).

Given the ambitious scope of the project and the "exponential proliferation" in the number of research papers on intermetallic compounds in the past decade, it was perhaps inevitable that this collective work would omit some key papers, particularly in fast-growing areas such as point defects and diffusion (Volume 1), and gamma TiAl and its alloys (Volume 2). Despite this shortcoming, this treatise's comprehensive discussion of crystal structure, the utility of its subject and author indexes and lists of acronyms and nomenclature, and the innovation of its index of compounds should significantly enhance further intermetallics research and development over the next few decades and should guarantee that this work will remain one of the key references on intermetallic compounds for a long time to come.

Reviewer: Man H. Yoo is a senior research staff member in the Metals and Ceramics Division, Oak Ridge National Laboratory. His research work includes physical properties and mechanical behavior of structural materials including intermetallic compounds.

Advertisers in This Issue

	Page No.
Bio-Rad Laboratories, Digilab Division	3
Cerac, Inc.	6
Commonwealth Scientific Corp.	21
High Voltage Engineering	inside front cover
Huntington Laboratories	outside back cover
Nagase America Corp.	35
Oxford Cryosystems	inside back cover
The Phosphor Technology Center	5
Tong Yang Central Laboratories	50
VAT, Inc.	41
Virginia Semiconductor, Inc.	53
Voltaix, Inc.	40
John Wiley & Sons	54
J A Woollam Co., Inc.	20

For free information about the products and services offered in this issue, fill out and mail the Reader Service Card, or FAX it to 312-922-3165.

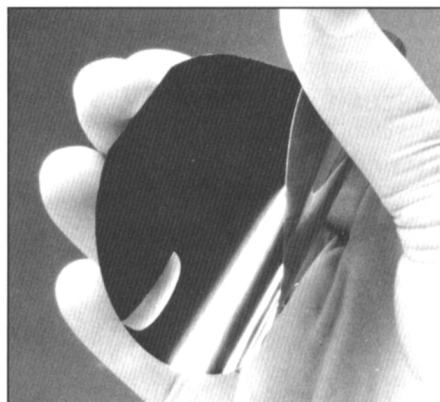
Send Books for Review to

MRS Bulletin
 Materials Research Society
 506 Keystone Drive
 Warrendale, PA 15086-7573 USA



We're the One

With Silicon Engineered For MEMS



A 10μ thin single crystal silicon membrane manufactured at Virginia Semiconductor, Inc.

- **THINK** 5 micron thin, <100> silicon membranes or any greater thickness needed; either Cz or Fz silicon !
- **THINK** <110> Fz silicon as thin as 100 microns !
- **THINK** Silicon membranes accurately measured at ± 1.0 micron !
- **THINK** Double side polished surfaces with (TTV's) at ≤ 2.5 microns !
- **THINK** Tailoring to your orientation and dopant needs !
- **THINK** Batch sizes of 10 wafers or more !
- **THINK** 50.8 - 100.0 mm diameters !
- **THINK**

VIRGINIA SEMICONDUCTOR, INC.

1501 Powhatan Street, Fredericksburg, VA 22401
 PH: (540) 373-2900 FAX: (540) 371-0371



Circle No. 11 On Reader Service Card